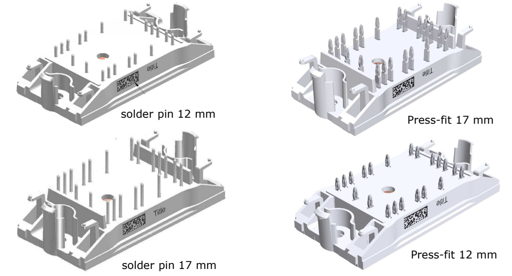
10-FZ06NPA070FP-P969F/ 10-F006NPA070FP-P969F09 10-PZ06NPA070FP-P969FY/ 10-P006NPA070FP-P969F09Y

*flow*NPC 0 — 600 V/75 A & 70 A PS*

Features

- *PS: 70A parallel switch (60A PT and 99mΩ)
- neutral point clamped inverter
- reactive power capability
- SiC buck diode
- low inductance layout

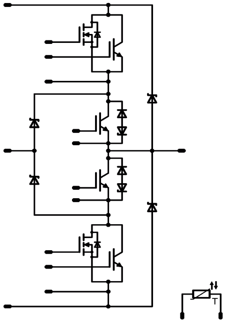
flow 0 housing



Target Applications

- solar inverter
- UPS

Schematic



Types

- 10-FZ06NPA070FP-P969F
- 10-F006NPA070FP-P969F09
- 10-PZ06NPA070FP-P969FY
- 10-P006NPA070FP-P969F09Y

Maximum Ratings

Tj=25℃, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Buck IGBT				
Collector-emitter break down voltage	V_{CE}		600	V
DC collector current	I_C	$T_j=T_j$max $T_h=80$℃ $T_c=80$℃	44 59	A
Repetitive peak collector current	I_{Cpulse}	t_p limited by $T_j$max	240	A
Power dissipation per IGBT	P_{tot}	$T_j=T_j$max $T_h=80$℃ $T_c=80$℃	71 108	W
Gate-emitter peak voltage	V_{GE}		±20	V
Short circuit ratings	t_{SC} V_{CC}	$T_j≤150$℃ $V_{GE}=15V$	5 390	µs V
Maximum Junction Temperature	$T_j$max		150	℃
Buck FWD				
Peak Repetitive Reverse Voltage	V_{RRM}	$T_j=25$℃	600	V
DC forward current	I_F	$T_j=T_j$max $T_h=80$℃ $T_c=80$℃	27 37	A
Repetitive peak forward current	I_{FRM}	t_p limited by $T_j$max $T_c=100$℃	105	A
Power dissipation per Diode	P_{tot}	$T_j=T_j$max $T_h=80$℃ $T_c=80$℃	50 75	W
Maximum Junction Temperature	$T_j$max		175	℃

Maximum Ratings

T_j=25℃, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Buck MOSFET					
Drain to source breakdown voltage	V_{DS}			600	V
DC drain current	I_D	T_j=$T_j$max	T_h=80℃ T_c=80℃	16 21	A
Pulsed drain current	I_{Dpulse}	t_p limited by $T_j$max	Tc=25℃	93	A
Power dissipation	P_{tot}	T_j=$T_j$max	T_h=80℃ T_c=80℃	54 97	W
Gate-source peak voltage	Vgs			±20	V
Maximum Junction Temperature	$T_j$max			150	℃
Boost IGBT					
Collector-emitter break down voltage	V_{CE}			600	V
DC collector current	I_C	T_j=$T_j$max	T_h=80℃ T_c=80℃	57 75	A
Repetitive peak collector current	I_{Cpuls}	t_p limited by $T_j$max		225	A
Power dissipation per IGBT	P_{tot}	T_j=$T_j$max	T_h=80℃ T_c=80℃	85 129	W
Gate-emitter peak voltage	V_{GE}			±20	V
Short circuit ratings	t_{SC} V_{CC}	T_j≤150℃ V_{GE}=15V		6 360	μs V
Maximum Junction Temperature	$T_j$max			175	℃
Boost Inverse Diode					
Peak Repetitive Reverse Voltage	V_{RRM}	T_c=25℃		600	V
DC forward current	I_F	T_j=$T_j$max	T_h=80℃ T_c=80℃	2	A
Power dissipation per Diode	P_{tot}	T_j=$T_j$max	T_h=80℃ T_c=80℃	21	W
Maximum Junction Temperature	$T_j$max			150	℃
Boost FWD					
Peak Repetitive Reverse Voltage	V_{RRM}	T_j=25℃		1200	V
DC forward current	I_F	T_j=$T_j$max	T_h=80℃ T_c=80℃	20 28	A
Repetitive peak forward current	I_{FRM}	t_p limited by $T_j$max		70	A
Power dissipation per Diode	P_{tot}	T_j=$T_j$max	T_h=80℃ T_c=80℃	34 52	W
Maximum Junction Temperature	$T_j$max			150	℃

Maximum Ratings

Tj=25℃, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	℃
Operation temperature under switching condition	T_{op}		-40…+(Tjmax - 25)	℃
Insulation Properties				
Insulation voltage	V_{is}	t=2s DC voltage	4000	V
Creepage distance			min 12,7	mm
Clearance			min 12,7	mm

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	
Buck IGBT *										
Gate emitter threshold voltage	$V_{GE(th)}$	VCE=VGE			0,00025	Tj=25℃ Tj=125℃	4,5	5,2	7	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		70	Tj=25℃ Tj=125℃	1	2,32 2,09	2,9	V
Collector-emitter cut-off current incl. Diode	I_{CES}		0	600		Tj=25℃ Tj=125℃			250	uA
Gate-emitter leakage current	I_{GES}		±20	0		Tj=25℃ Tj=125℃			300	nA
Integrated Gate resistor	R_{gint}							none		Ω
Input capacitance **	C_{ies}	f=1MHz	0	25		Tj=25℃		4+4,7		nF
Output capacitance	C_{oss}							400		pF
Reverse transfer capacitance	C_{rss}							200		
Gate charge **	Q_{Gate}		±15			Tj=25℃		225+70		nC
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						0,99		K/W

* see dinamic characteristic at **Buck MosFET**
**additional value stands for built-in capacitor

Buck FWD										
Diode forward voltage	V_F				24	Tj=25℃ Tj=125℃	1	1,48 1,58	1,8	V
Reverse leakage current	I_r			600		Tj=25℃ Tj=125℃			600	µA
Peak reverse recovery current	I_{RRM}	Rgon=8 Ω		350	40	Tj=25℃ Tj=125℃		42 34		A
Reverse recovery time	t_{rr}					Tj=25℃ Tj=125℃		9 9		ns
Reverse recovered charge	Q_{rr}					Tj=25℃ Tj=125℃		0,121 0,121		µC
Peak rate of fall of recovery current	di(rec)max /dt					Tj=25℃ Tj=125℃		13108 10427		A/µs
Reverse recovered energy	Erec					Tj=25℃ Tj=125℃		0,011 0,012		mWs
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						1,91		K/W
Buck MOSFET										
Static drain to source ON resistance	$R_{ds(on)}$		10		18	Tj=25℃ Tj=125℃		109 219		mΩ
Gate threshold voltage	$V_{(GS)th}$			V_{DS}=V_{GS}	0,001	Tj=25℃ Tj=125℃	2,1	3	3,6	V
Gate to Source Leakage Current	I_{gss}		20	0		Tj=25℃ Tj=125℃			200	nA
Zero Gate Voltage Drain Current	I_{dss}		0	600		Tj=25℃ Tj=125℃			60	uA
Turn On Delay Time	$t_{d(ON)}$	Rgon=8 Ω ** Rgoff=8 Ω **	±15	350	40	Tj=25℃ Tj=125℃		92 101		ns
Rise Time	t_r					Tj=25℃ Tj=125℃		6 6		
Turn off delay time	$t_{d(OFF)}$					Tj=25℃ Tj=125℃		208 210		
Fall time	t_f					Tj=25℃ Tj=125℃		9 5		
Turn-on energy loss per pulse	E_{on}					Tj=25℃ Tj=125℃		0,066 0,096		mWs
Turn-off energy loss per pulse	E_{off}					Tj=25℃ Tj=125℃		0,100 0,225		
Total gate charge	Q_g		±15	350	40	Tj=25℃		60	80	nC
Gate to source charge	Q_{gs}							14		
Gate to drain charge	Q_{gd}							20		
Input capacitance	C_{iss}	f=1MHz	0	100		Tj=25℃		2800		pF
Output capacitance	C_{oss}							130		
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						1,29		K/W

** see schematic of the Gate-complex at characteristic figures

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	
Boost IGBT										
Gate emitter threshold voltage	$V_{GE(th)}$	V_{CE}=V_{GE}			0,0012	Tj=25℃ Tj=125℃	5	5,8	6,5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		70	Tj=25℃ Tj=125℃	1	1,49 1,6	2,1	V
Collector-emitter cut-off incl diode	I_{CES}		0	600		Tj=25℃ Tj=125℃			0,03	mA
Gate-emitter leakage current	I_{GES}		20	0		Tj=25℃ Tj=125℃			650	nA
Integrated Gate resistor	R_{gint}							none		Ω
Turn-on delay time	$t_{d(on)}$	Rgon=8 Ω Rgoff=8 Ω	±15	350	40	Tj=25℃ Tj=125℃		37 35		ns
Rise time	t_r					Tj=25℃ Tj=125℃		13 16		
Turn-off delay time	$t_{d(off)}$					Tj=25℃ Tj=125℃		459 500		
Fall time	t_f					Tj=25℃ Tj=125℃		83 106		
Turn-on energy loss per pulse	E_{on}					Tj=25℃ Tj=125℃		0,81 1,11		mWs
Turn-off energy loss per pulse	E_{off}					Tj=25℃ Tj=125℃		1,35 1,71		
Input capacitance	C_{ies}	f=1MHz	0	25		Tj=25℃		4620		pF
Output capacitance	C_{oss}							288		
Reverse transfer capacitance	C_{rss}							137		
Gate charge	Q_{Gate}		15	480	75	Tj=25℃		470		nC
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						1,11		K/W
Boost Inverse Diode										
Diode forward voltage	V_F				20	Tj=25℃ Tj=125℃		9,07 9,43		V
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						4,36		K/W
Boost FWD										
Diode forward voltage	V_F				30	Tj=25℃ Tj=125℃	1,5	2,44 2,01	3,5	V
Reverse leakage current	I_r			1200		Tj=25℃ Tj=125℃			100	µA
Peak reverse recovery current	I_{RRM}	Rgon=8 Ω		350	40	Tj=25℃ Tj=125℃		80 100		A
Reverse recovery time	t_{rr}					Tj=25℃ Tj=125℃		33 109		ns
Reverse recovered charge	Q_{rr}					Tj=25℃ Tj=125℃		2,7 6		µC
Peak rate of fall of recovery current	di(rec)max /dt					Tj=25℃ Tj=125℃		11226 8793		A/µs
Reverse recovery energy	E_{rec}					Tj=25℃ Tj=125℃		0,61 1,52		mWs
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						2,04		K/W
Thermistor										
Rated resistance*	R_{25}	Tol. ±13%				Tj=25℃	19,1	22	24,9	kΩ
	R_{100}	Tol. ±5%				Tj=100℃	1411	1486	1560	Ω
Power dissipation	P					Tj=25℃		210		mW
B-value	$B_{(25/100)}$	Tol. ±3%				Tj=25℃		4000		K

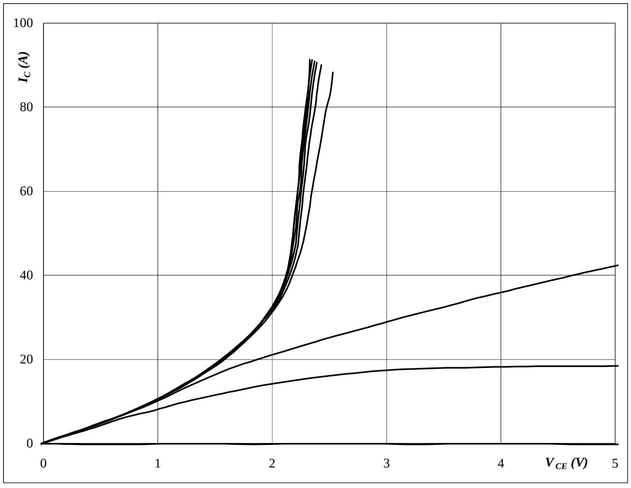
* see details on **Thermistor** charts on **Figure 2.**

Buck

Figure 1 MOSFET

Typical output characteristics

$I_C = f(V_{CE})$



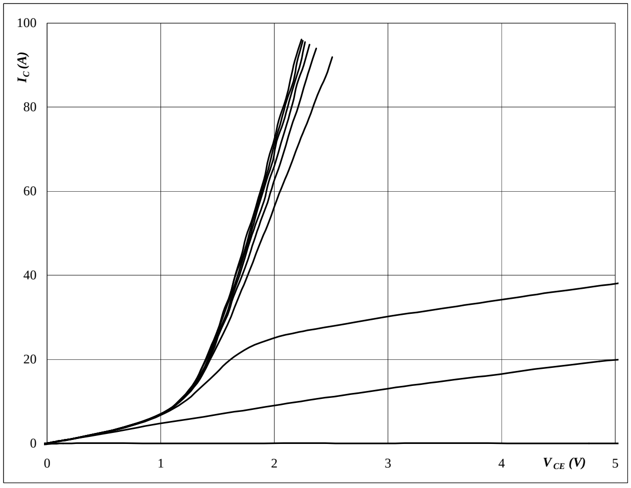
At

t_p = 250 µs
T_j = 25 ℃
V_{GE} from 3 V to 19 V in steps of 2 V

Figure 2 MOSFET

Typical output characteristics

$I_C = f(V_{CE})$



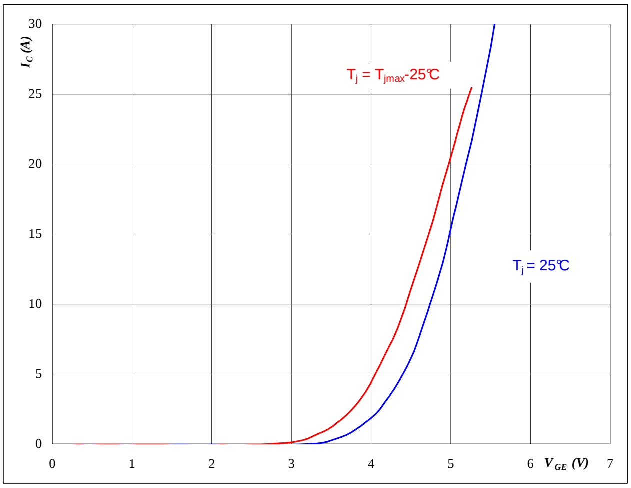
At

t_p = 250 µs
T_j = 125 ℃
V_{GE} from 3 V to 19 V in steps of 2 V

Figure 3 MOSFET

Typical transfer characteristics

$I_C = f(V_{GE})$



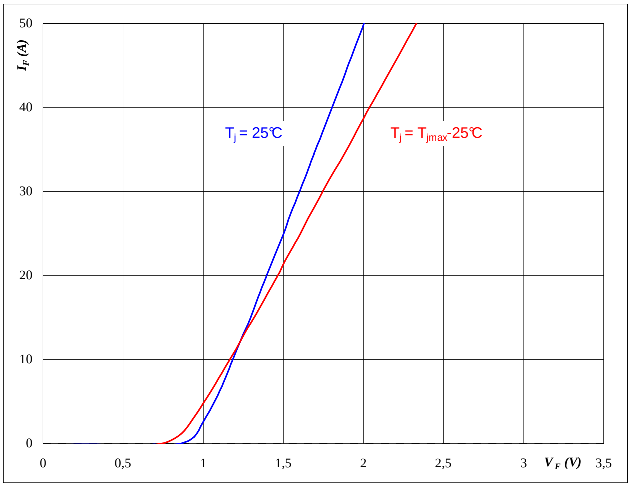
At

t_p = 250 µs
V_{CE} = 10 V

Figure 4 FWD

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

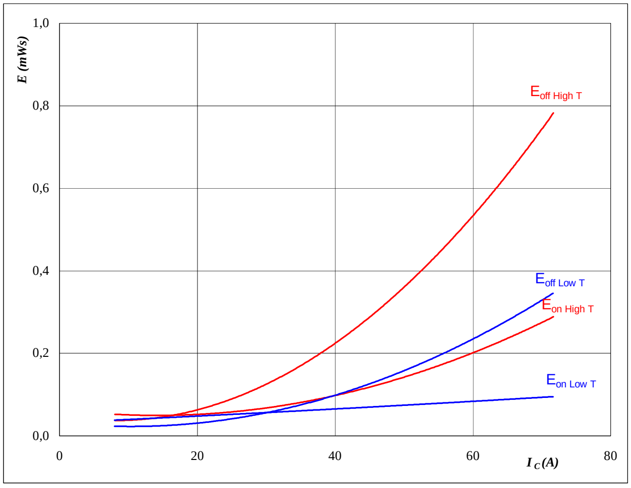
t_p = 250 µs

Buck

Figure 5 MOSFET

Typical switching energy losses
as a function of collector current

$E = f(I_C)$



With an inductive load at

T_j =	25/125	℃
V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	8	Ω
R_{goff}=	8	Ω

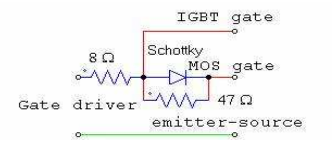
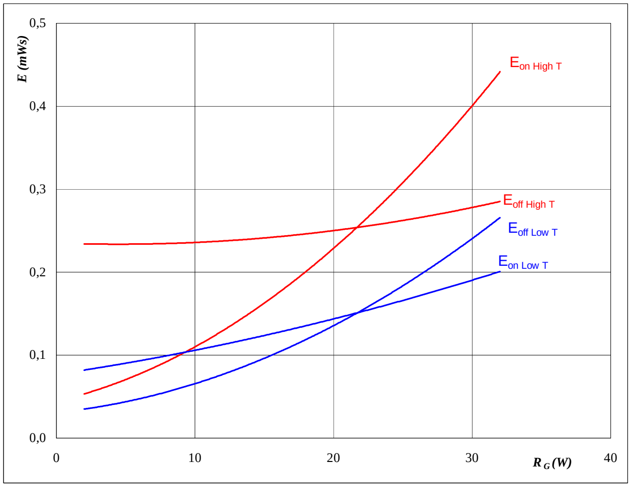


Figure 6 MOSFET

Typical switching energy losses
as a function of IGBT gate resistor

$E = f(R_G)$



With an inductive load at

T_j =	25/125	℃
V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	40	A

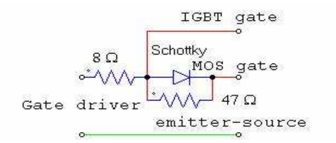
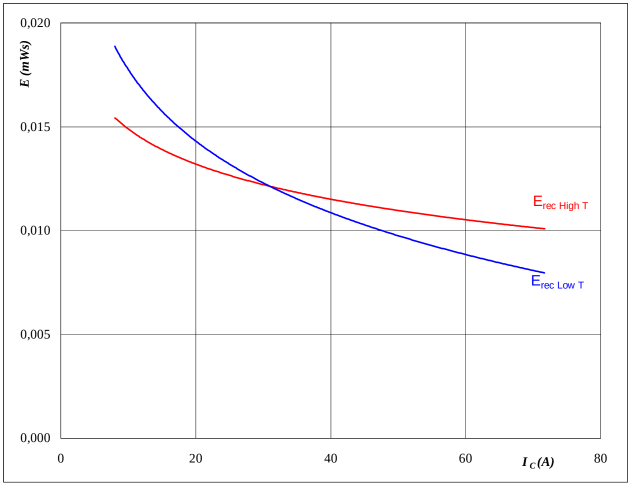


Figure 7 FWD

Typical reverse recovery energy loss
as a function of collector current

$E_{rec} = f(I_c)$



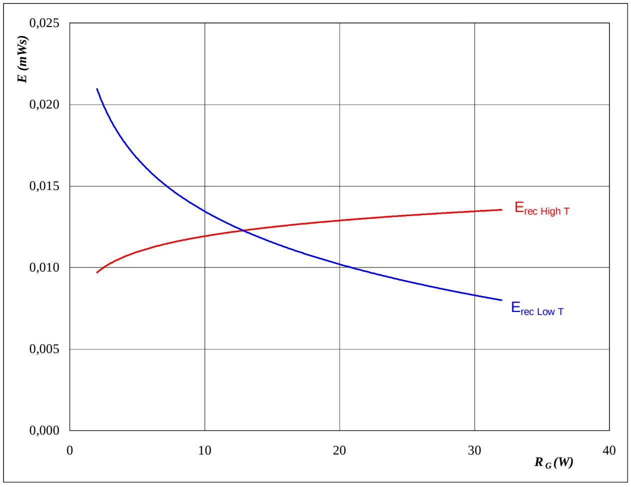
With an inductive load at

T_j =	25/125	℃
V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	8	Ω

Figure 8 FWD

Typical reverse recovery energy loss
as a function of gate resistor

$E_{rec} = f(R_G)$



With an inductive load at

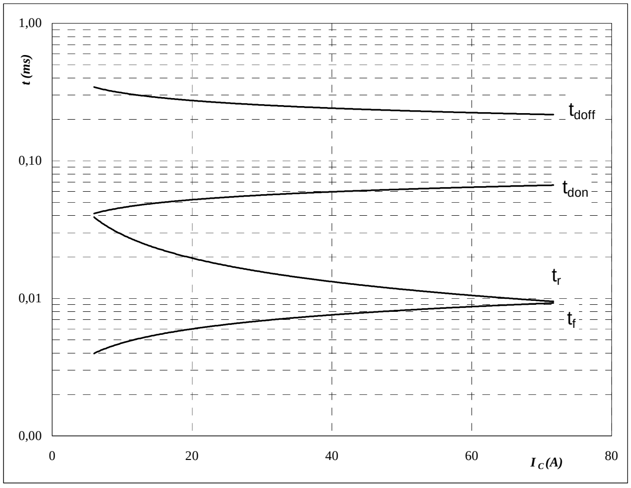
T_j =	25/125	℃
V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	40	A

Buck

Figure 9 MOSFET

Typical switching times as a function of collector current

t = f(I_C)



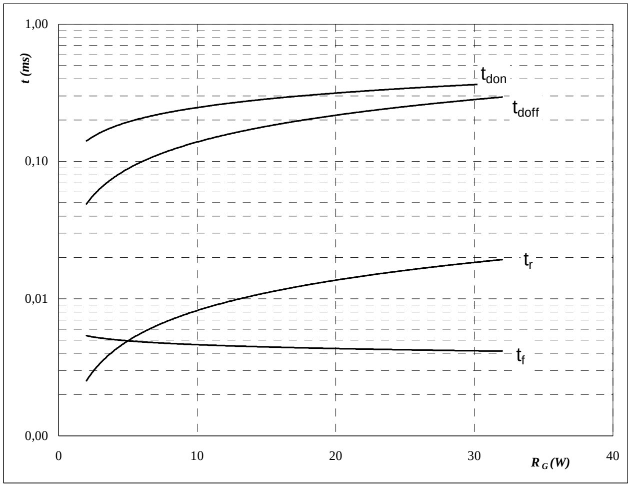
With an inductive load at

T_j = 125 ℃
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 8 Ω
R_{goff} = 8 Ω

Figure 10 MOSFET

Typical switching times as a function of gate resistor

t = f(R_G)



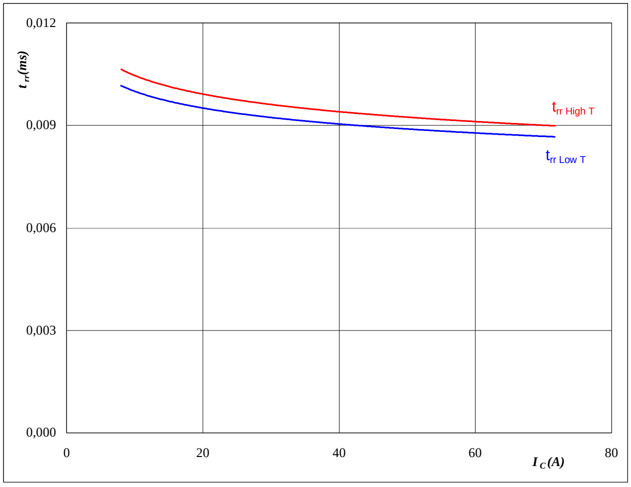
With an inductive load at

T_j = 125 ℃
V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 40 A

Figure 11 FWD

Typical reverse recovery time as a function of collector current

t_{rr} = f(Ic)



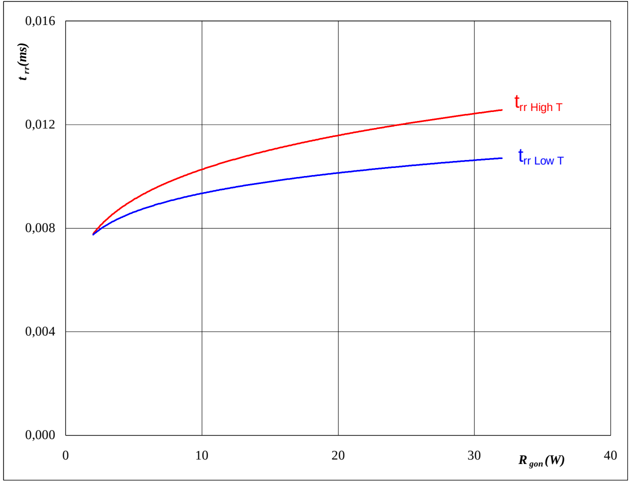
At

T_j = 25/125 ℃
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 8 Ω

Figure 12 FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



At

T_j = 25/125 ℃
V_R = 350 V
I_F = 40 A
V_{GE} = ±15 V

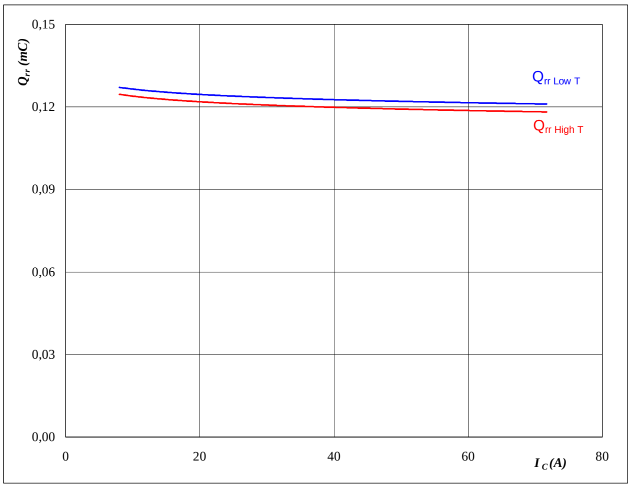
Buck

Figure 13

FWD

Typical reverse recovery charge as a function of collector current

$Q_{rr} = f(I_C)$



At

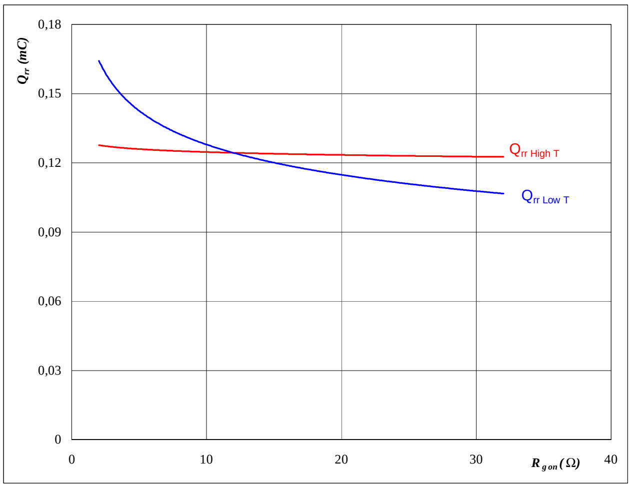
T_j = 25/125 ℃
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 8 Ω

Figure 14

FWD

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$Q_{rr} = f(R_{gon})$



At

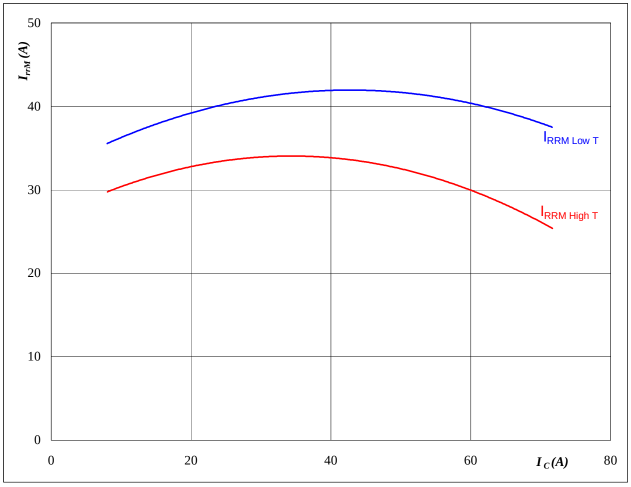
T_j = 25/125 ℃
V_R = 350 V
I_F = 40 A
V_{GE} = ±15 V

Figure 15

FWD

Typical reverse recovery current as a function of collector current

$I_{RRM} = f(I_C)$



At

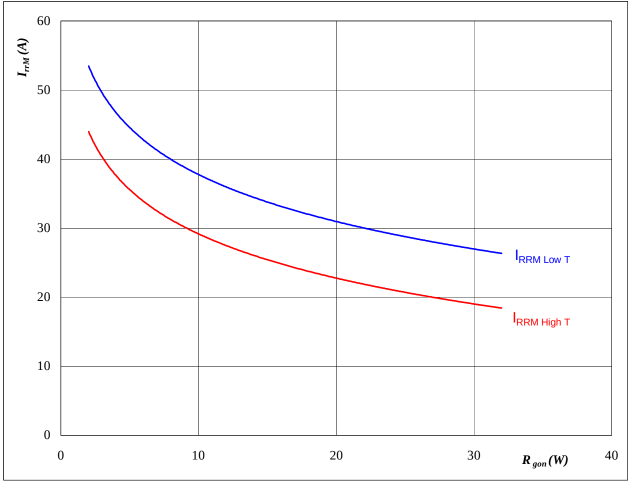
T_j = 25/125 ℃
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 8 Ω

Figure 16

FWD

Typical reverse recovery current as a function of IGBT turn on gate resistor

$I_{RRM} = f(R_{gon})$



At

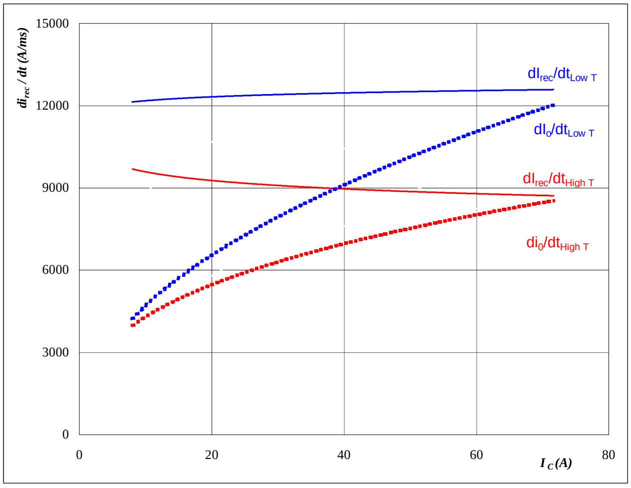
T_j = 25/125 ℃
V_R = 350 V
I_F = 40 A
V_{GE} = ±15 V

Buck

Figure 17 FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current

$dI_0/dt, dI_{rec}/dt = f(Ic)$



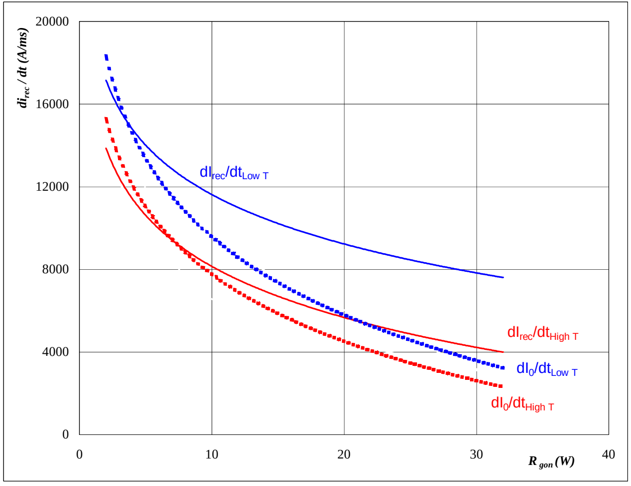
At

T_j =	25/125	℃
V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	8	Ω

Figure 18 FWD

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$dI_0/dt, dI_{rec}/dt = f(R_{gon})$



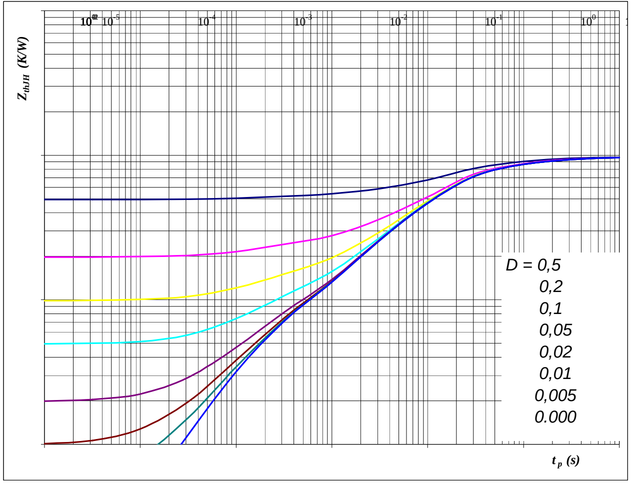
At

T_j =	25/125	℃
V_R =	350	V
I_F =	40	A
V_{GE} =	±15	V

Figure 19 IGBT

IGBT transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D =	t_p / T	
R_{thJH} =	0,99	K/W

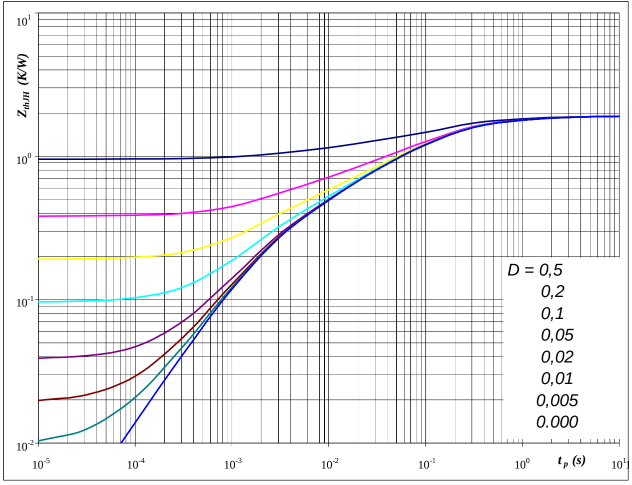
IGBT thermal model values

R (C/W)	Tau (s)
0,06	9,7E+00
0,18	9,9E-01
0,56	1,6E-01
0,14	2,4E-02
0,05	1,6E-03

Figure 20 FWD

FWD transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D =	t_p / T	
R_{thJH} =	1,91	K/W

FWD thermal model values

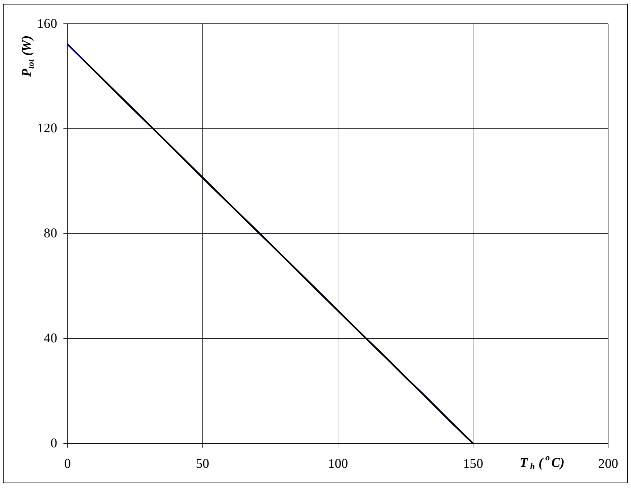
R (C/W)	Tau (s)
0,10	3,8E+00
0,32	5,7E-01
0,91	1,0E-01
0,38	1,4E-02
0,21	2,0E-03

Buck

Figure 21 IGBT

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



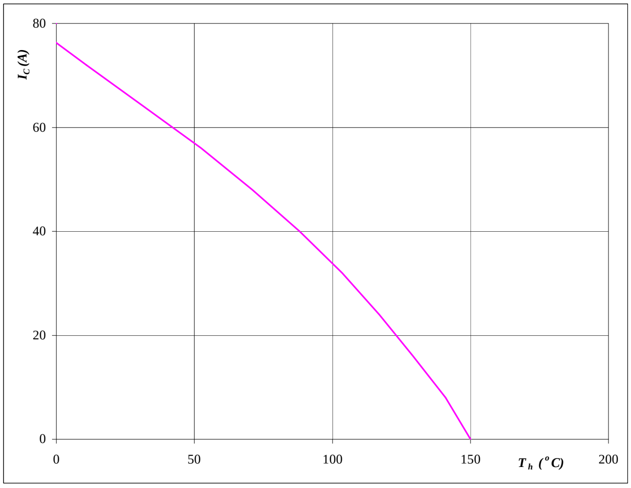
At

T_j = 150 ℃

Figure 22 IGBT

Collector current as a function of heatsink temperature

$I_C = f(T_h)$



At

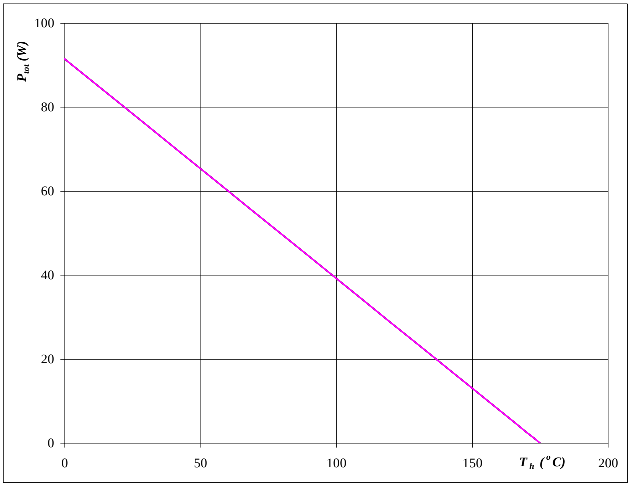
T_j = 150 ℃

V_{GE} = 15 V

Figure 23 FWD

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



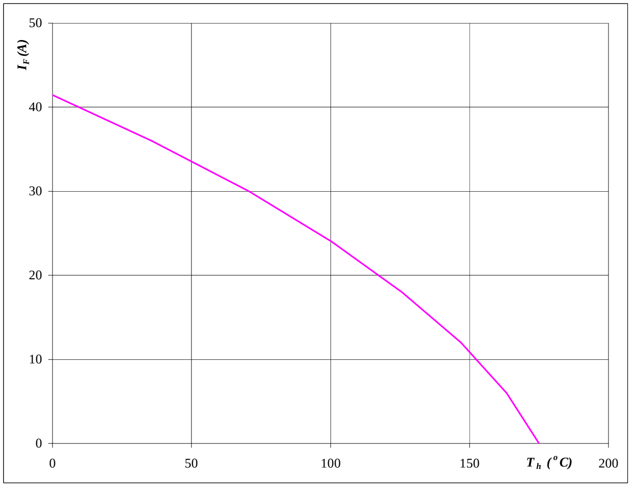
At

T_j = 175 ℃

Figure 24 FWD

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

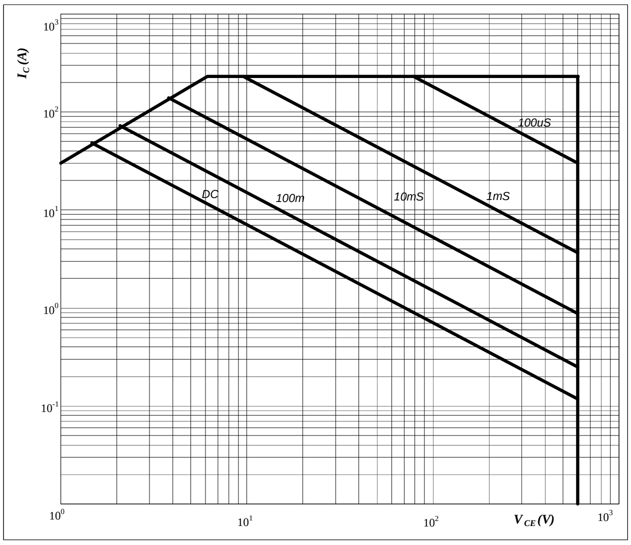
T_j = 175 ℃

Buck

Figure 25 IGBT

Safe operating area as a function of collector-emitter voltage

$I_C = f(V_{CE})$



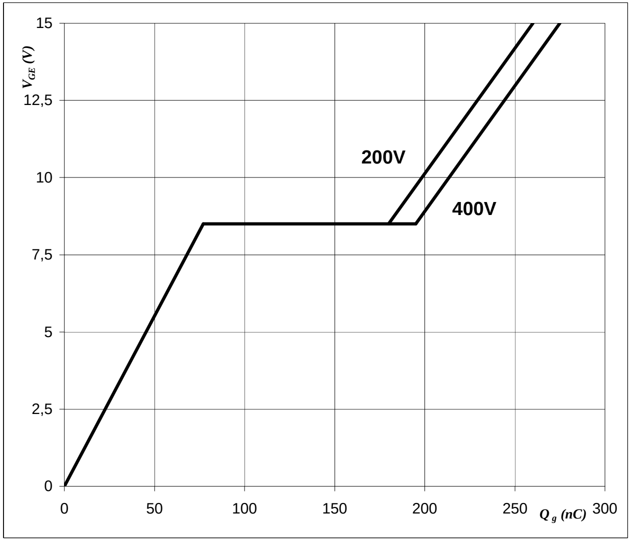
At

D =	single pulse	
Th =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	ºC

Figure 26 IGBT

Gate voltage vs Gate charge

$V_{GE} = f(Q_g)$



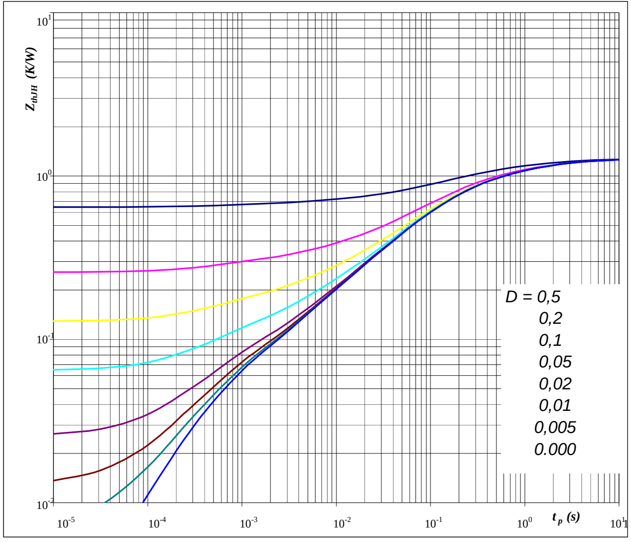
At

$I_{G(REF)}$=1mA, R_L=15Ω

Figure 27 MOSFET

MOSFET transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



D =	t_p / T	
R_{thJH} =	1,29	K/W

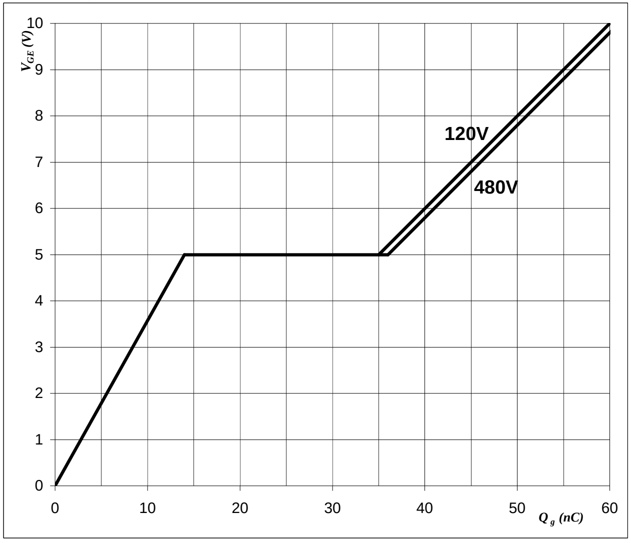
MOSFET thermal model

R (C/W)	Tau (s)
0,09	9,2E+00
0,27	1,3E+00
0,53	2,1E-01
0,27	4,0E-02
0,08	4,8E-03
0,05	4,7E-04

Figure 28 MOSFET

Gate voltage vs Gate charge

$V_{GE} = f(Q_g)$



At

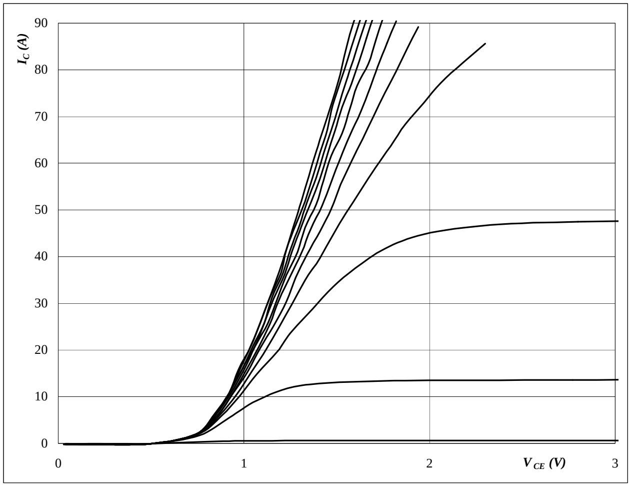
I_C =	18	A

Boost

Figure 1 IGBT

Typical output characteristics

$I_C = f(V_{CE})$



At

t_p = 250 µs

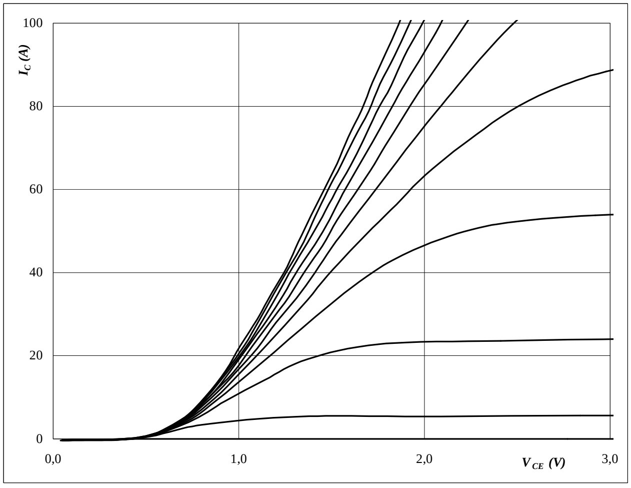
T_j = 25 ℃

V_{GE} from 7 V to 17 V in steps of 1 V

Figure 2 IGBT

Typical output characteristics

$I_C = f(V_{CE})$



At

t_p = 250 µs

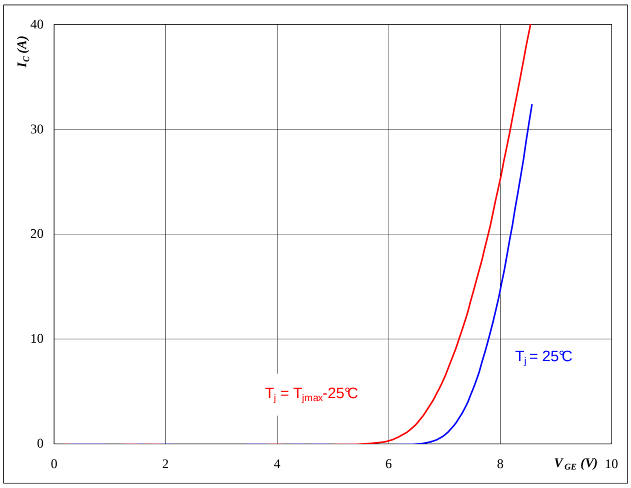
T_j = 125 ℃

V_{GE} from 6 V to 16 V in steps of 1 V

Figure 3 IGBT

Typical transfer characteristics

$I_C = f(V_{GE})$



At

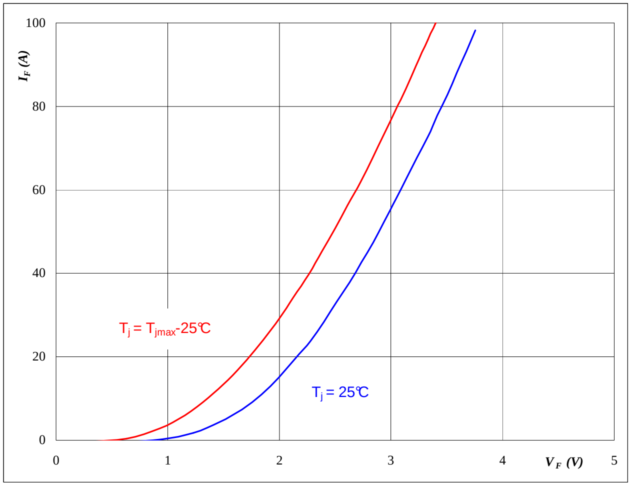
t_p = 250 µs

V_{CE} = 10 V

Figure 4 FWD

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

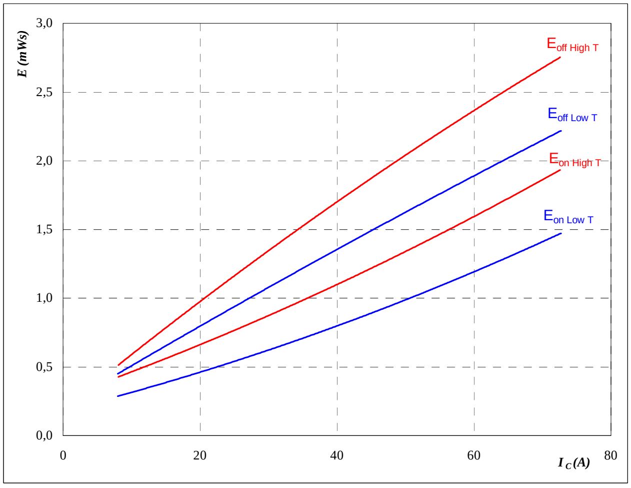
t_p = 250 µs

Boost

Figure 5 IGBT

Typical switching energy losses
as a function of collector current

$E = f(I_C)$



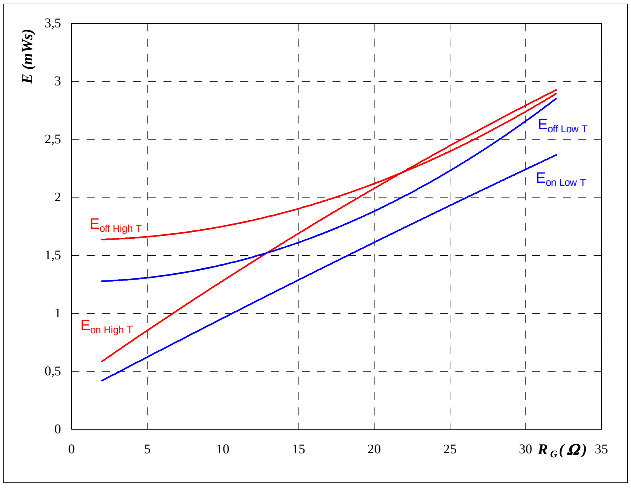
With an inductive load at

T_j = 25/125 ℃
V_{CE} = 350 V
V_{GE} = 15 V
R_{gon} = 8 Ω
R_{goff} = 8 Ω

Figure 6 IGBT

Typical switching energy losses
as a function of gate resistor

$E = f(R_G)$



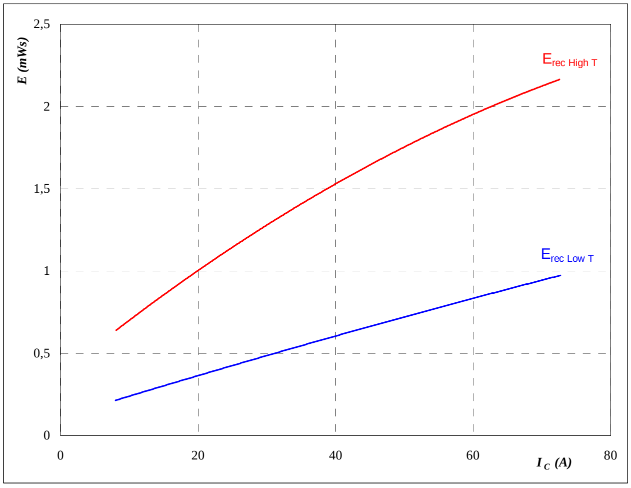
With an inductive load at

T_j = 25/125 ℃
V_{CE} = 350 V
V_{GE} = 15 V
I_C = 40 A

Figure 7 IGBT

Typical reverse recovery energy loss
as a function of collector current

$E_{rec} = f(I_c)$



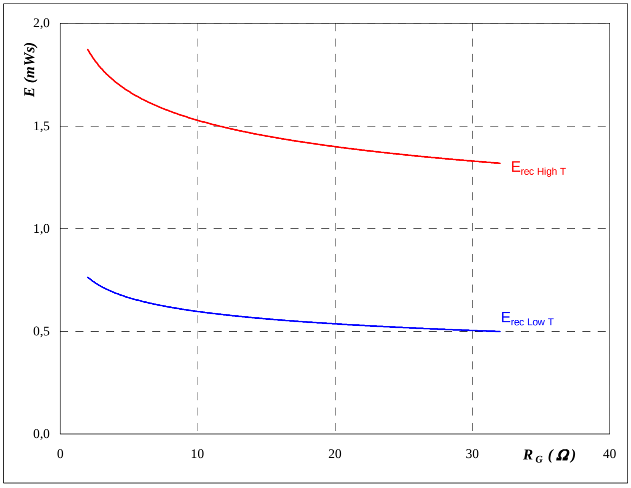
With an inductive load at

T_j = 25/125 ℃
V_{CE} = 350 V
V_{GE} = 15 V
R_{gon} = 8 Ω

Figure 8 IGBT

Typical reverse recovery energy loss
as a function of gate resistor

$E_{rec} = f(R_G)$



With an inductive load at

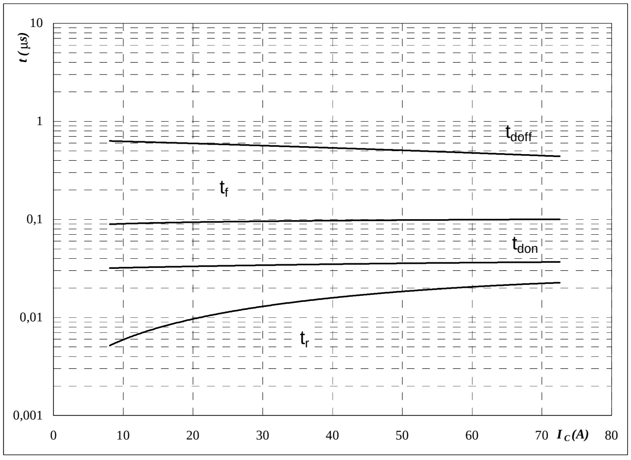
T_j = 25/125 ℃
V_{CE} = 350 V
V_{GE} = 15 V
I_C = 40 A

Boost

Figure 9 IGBT

Typical switching times as a function of collector current

t = f(I_C)



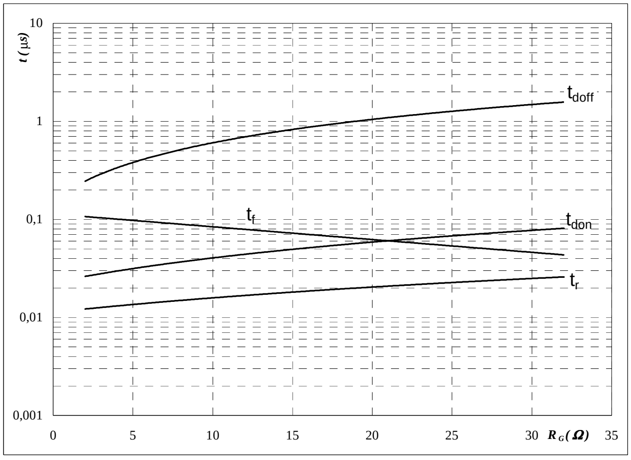
With an inductive load at

T_j =	125	℃
V_{CE} =	350	V
V_{GE} =	15	V
R_{gon} =	8	Ω
R_{goff} =	8	Ω

Figure 10 IGBT

Typical switching times as a function of gate resistor

t = f(R_G)



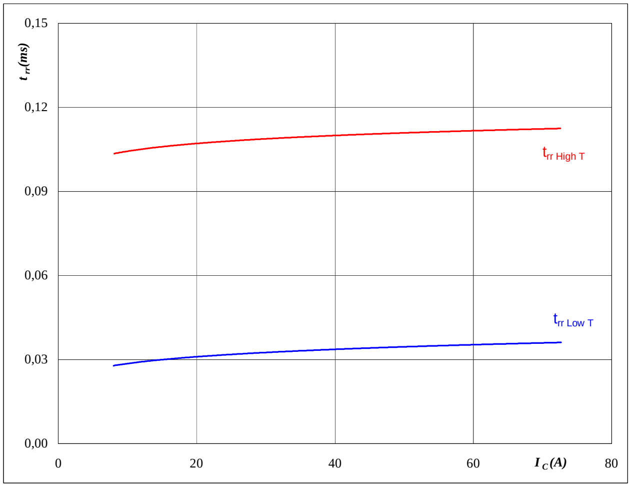
With an inductive load at

T_j =	125	℃
V_{CE} =	350	V
V_{GE} =	15	V
I_C =	40	A

Figure 11 FWD

Typical reverse recovery time as a function of collector current

t_{rr} = f(Ic)



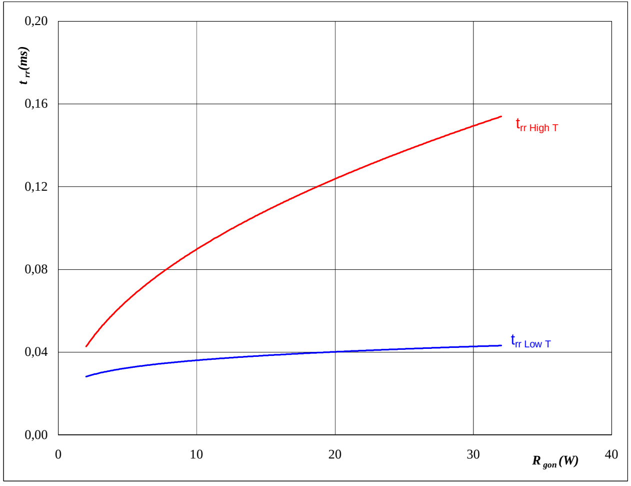
At

T_j =	25/125	℃
V_{CE} =	350	V
V_{GE} =	15	V
R_{gon} =	8	Ω

Figure 12 FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



At

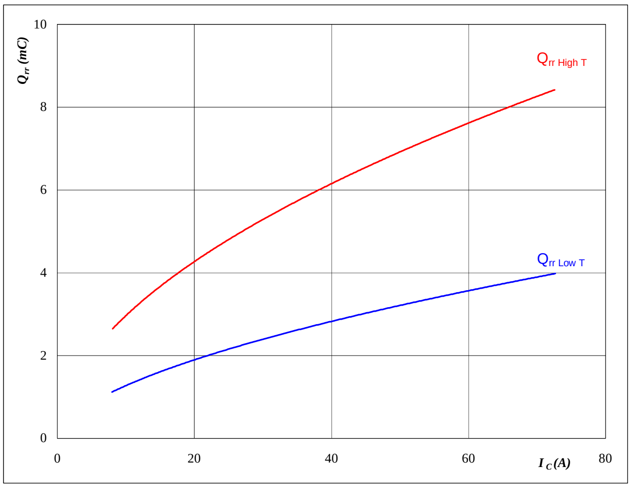
T_j =	25/125	℃
V_R =	350	V
I_F =	40	A
V_{GE} =	15	V

Boost

Figure 13 FWD

Typical reverse recovery charge as a function of collector current

$Q_{rr} = f(I_C)$



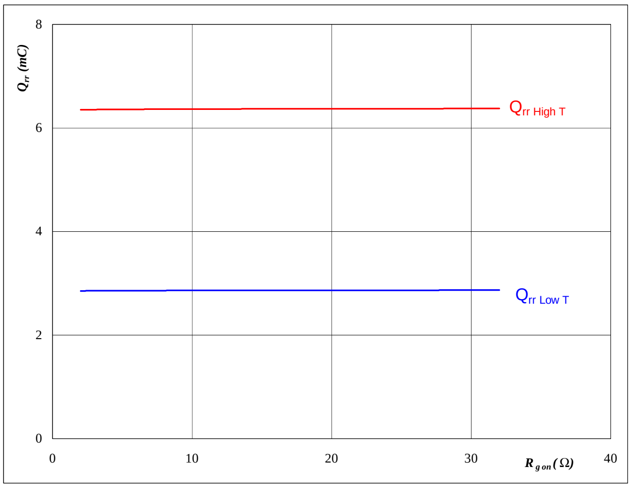
At

T_j =	25/125	℃
V_{CE} =	350	V
V_{GE} =	15	V
R_{gon} =	8	Ω

Figure 14 FWD

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$Q_{rr} = f(R_{gon})$



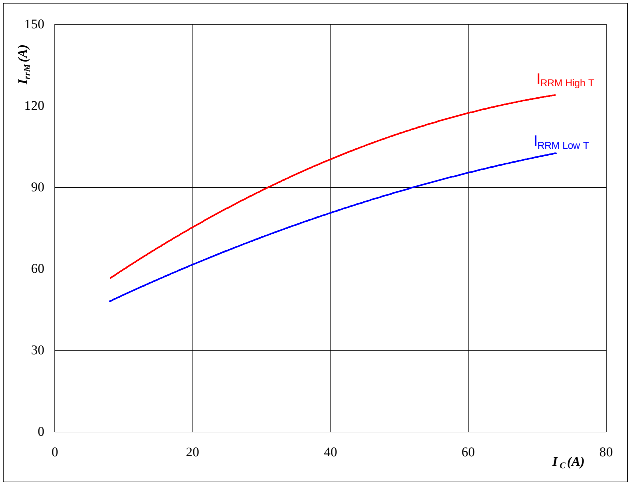
At

T_j =	25/125	℃
V_R =	350	V
I_F =	40	A
V_{GE} =	15	V

Figure 15 FWD

Typical reverse recovery current as a function of collector current

$I_{RRM} = f(I_C)$



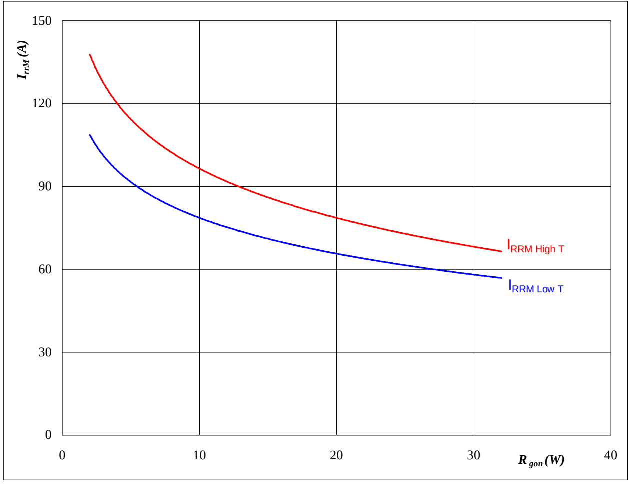
At

T_j =	25/125	℃
V_{CE} =	350	V
V_{GE} =	15	V
R_{gon} =	8	Ω

Figure 16 FWD

Typical reverse recovery current as a function of IGBT turn on gate resistor

$I_{RRM} = f(R_{gon})$



At

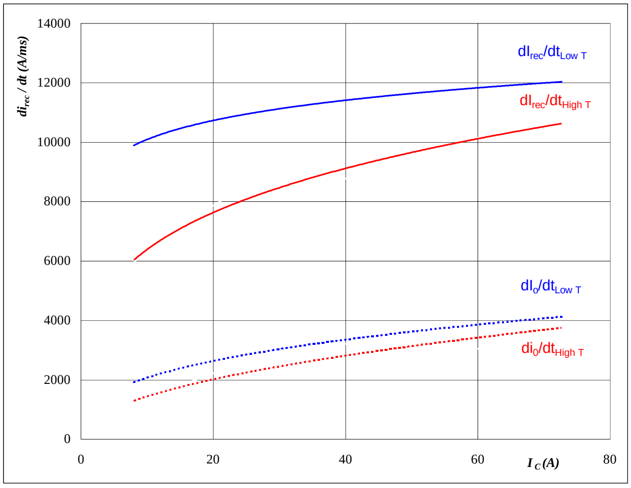
T_j =	25/125	℃
V_R =	350	V
I_F =	40	A
V_{GE} =	15	V

Boost

Figure 17 FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current

$dI_0/dt, dI_{rec}/dt = f(Ic)$



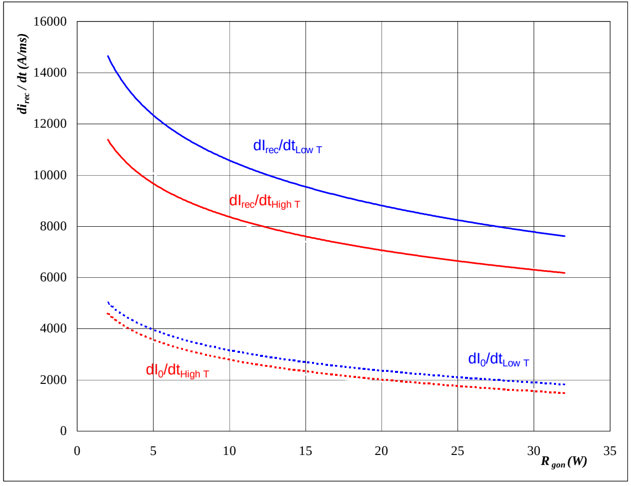
At

$T_j =$ 25/125 ℃
$V_{CE} =$ 350 V
$V_{GE} =$ 15 V
$R_{gon} =$ 8 Ω

Figure 18 FWD

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$dI_0/dt, dI_{rec}/dt = f(R_{gon})$



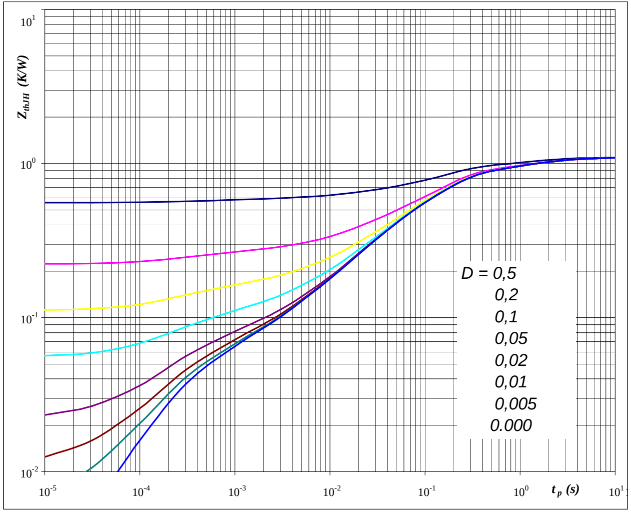
At

$T_j =$ 25/125 ℃
$V_R =$ 350 V
$I_F =$ 40 A
$V_{GE} =$ 15 V

Figure 19 IGBT

IGBT transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D = tp / T
$R_{thJH} =$ 1,11 K/W

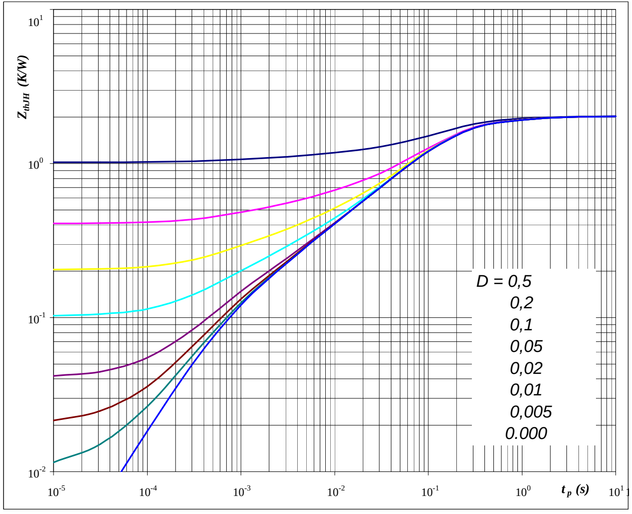
IGBT thermal model values

R (C/W)	Tau (s)
0,06	9,9E+00
0,22	1,2E+00
0,59	1,4E-01
0,17	2,2E-02
0,03	2,7E-03
0,04	2,7E-04

Figure 20 FWD

FWD transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D = tp / T
$R_{thJH} =$ 2,04 K/W

FWD thermal model values

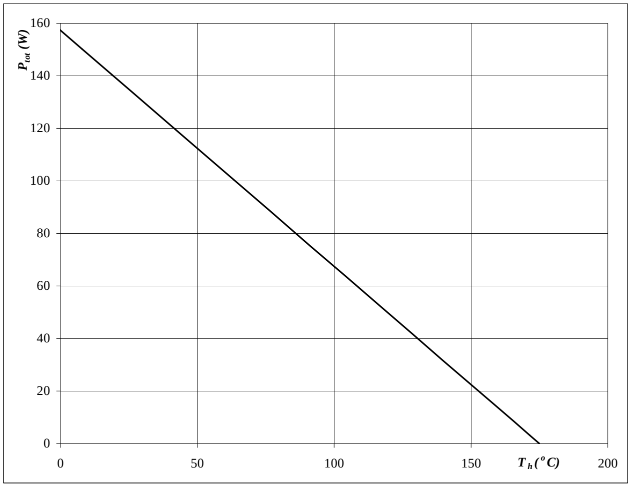
R (C/W)	Tau (s)
0,04	9,8E+00
0,21	1,0E+00
1,12	1,5E-01
0,42	3,7E-02
0,17	4,4E-03
0,08	6,1E-04

Boost

Figure 21 IGBT

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



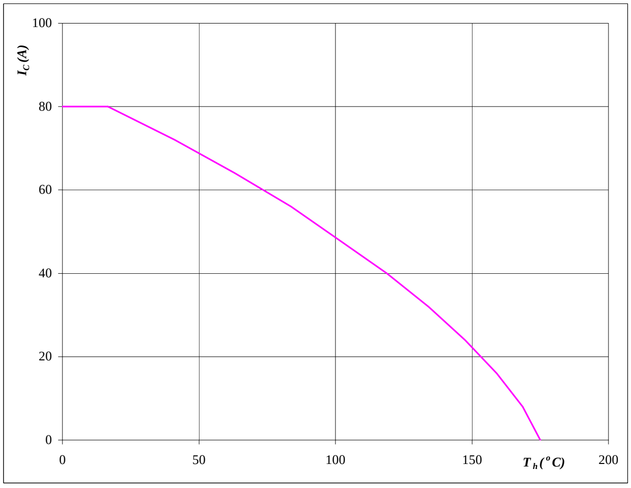
At

T_j = 175 ºC

Figure 22 IGBT

Collector current as a function of heatsink temperature

$I_C = f(T_h)$



At

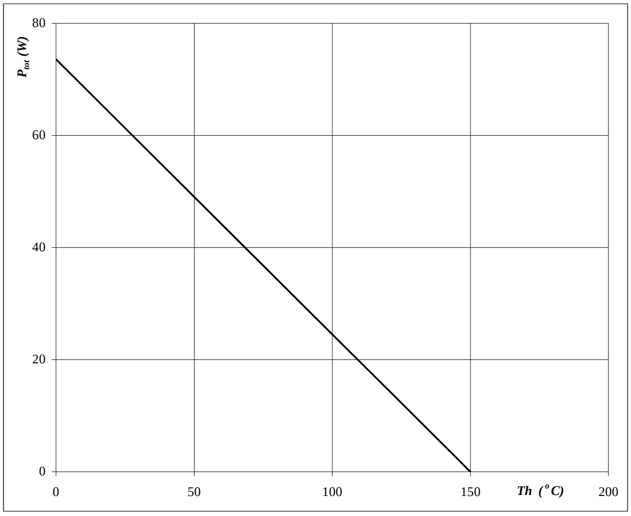
T_j = 175 ºC

V_{GE} = 15 V

Figure 23 FWD

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



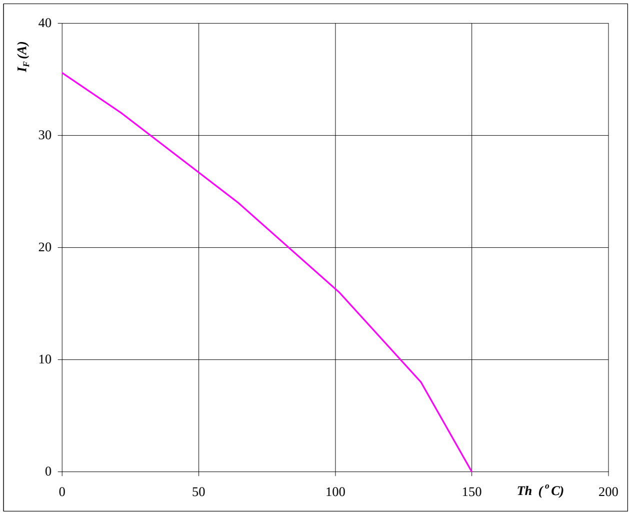
At

T_j = 150 ºC

Figure 24 FWD

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

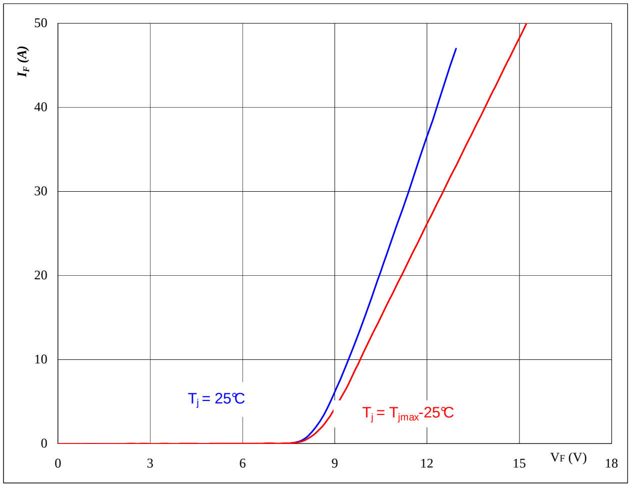
T_j = 150 ºC

Boost

Figure 25 Boost Inverse Diode

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



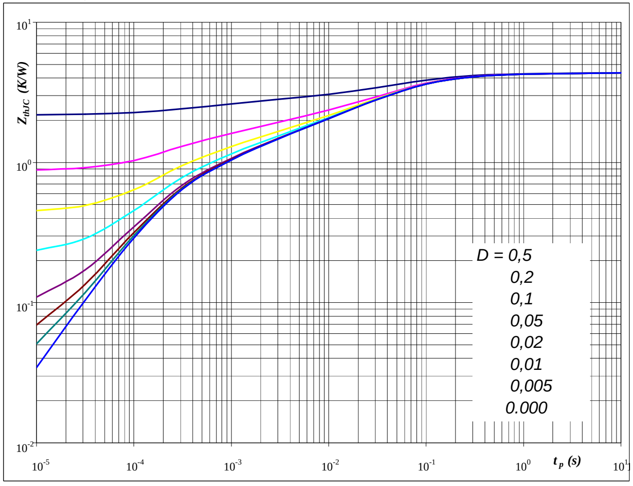
At

t_p = 250 µs

Figure 26 Boost Inverse Diode

Diode transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

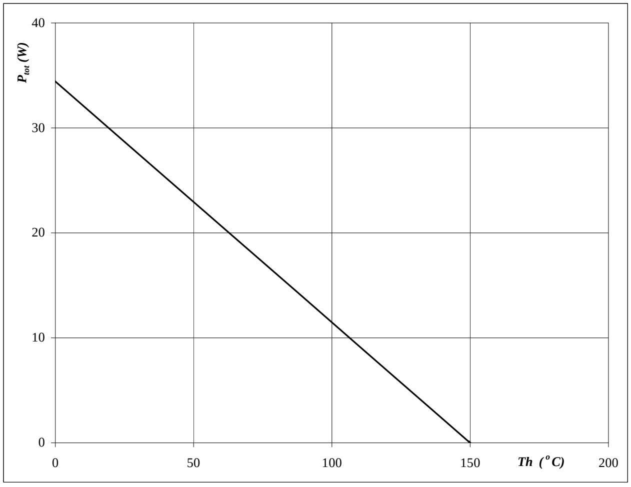
D = tp / T

R_{thJH} = 4,36 K/W

Figure 27 Boost Inverse Diode

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



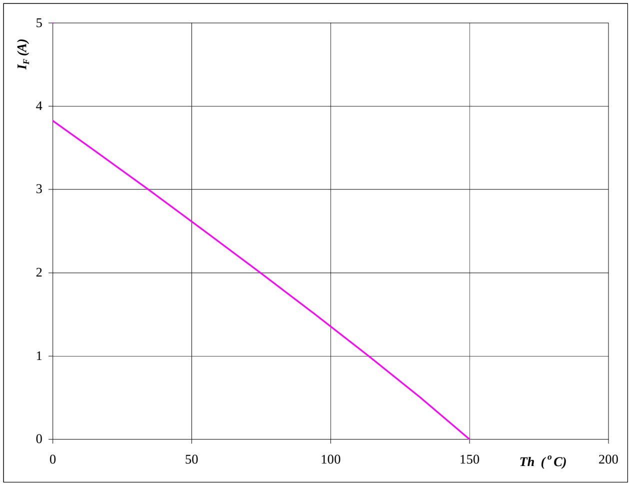
At

T_j = 150 ºC

Figure 28 Boost Inverse Diode

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

T_j = 150 ºC

Thermistor

Figure 1 Thermistor

Typical NTC characteristic as a function of temperature

$R_T = f(T)$

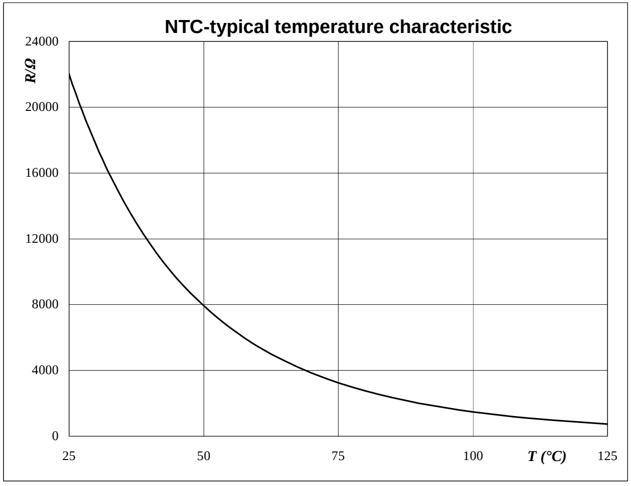


Figure 2 Thermistor

Typical NTC resistance values

$$R(T) = R_{25} \cdot e^{\left(B_{25/100} \cdot \left(\frac{1}{T} - \frac{1}{T_{25}}\right)\right)} \quad [\Omega]$$

T [°C]	R_{nom} [Ω]	R_{min} [Ω]	R_{max} [Ω]	△R/R [±%]
-55	2089434,5	1506495,4	2672373,6	27,9
0	71804,2	59724,4	83884	16,8
10	43780,4	37094,4	50466,5	15,3
20	27484,6	23684,6	31284,7	13,8
25	22000	19109,3	24890,7	13,1
30	17723,3	15512,2	19934,4	12,5
60	5467,9	4980,6	5955,1	8,9
70	3848,6	3546	4151,1	7,9
80	2757,7	2568,2	2947,1	6,9
90	2008,9	1889,7	2128,2	5,9
100	**1486,1**	**1411,8**	**1560,4**	**5**
150	400,2	364,8	435,7	8,8

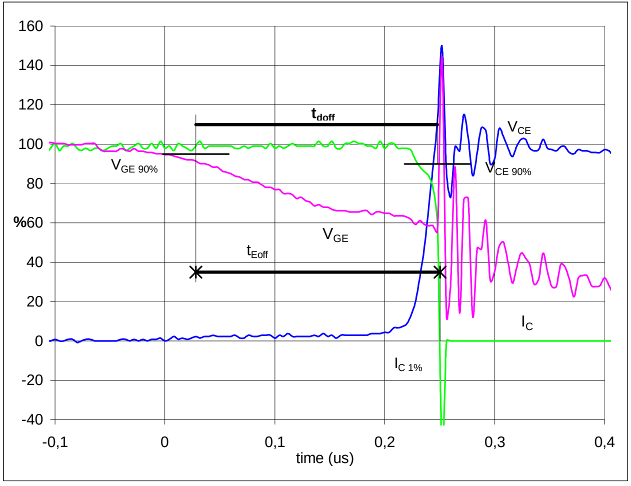
Switching Definitions BUCK MOSFET

General conditions

		T_j = 125 ℃			
$R_{gon\ IGBT}$	=	8 Ω	$R_{gon\ MOSFET}$	=	0 Ω
$R_{goff\ IGBT}$	=	8 Ω	$R_{goff\ MOSFET}$	=	47 Ω

Figure 1 Output inverter IGBT

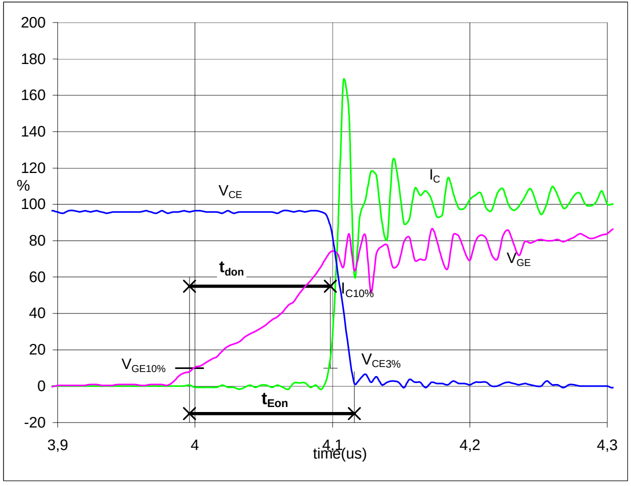
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff}
(t_{Eoff} = integrating time for E_{off})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	700	V
I_C (100%) =	40	A
t_{doff} =	0,21	µs
t_{Eoff} =	0,22	µs

Figure 2 Output inverter IGBT

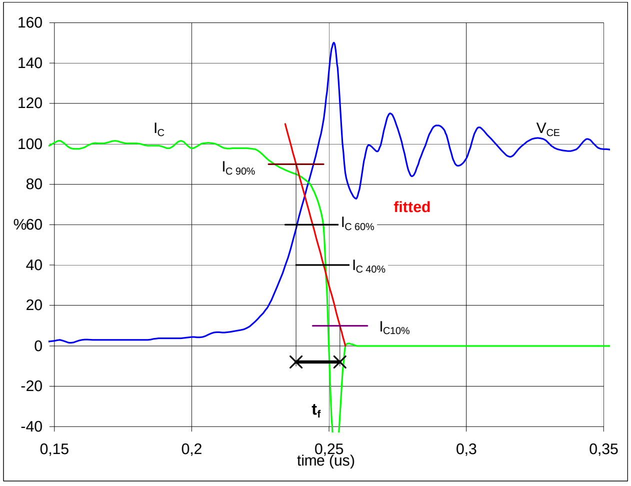
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon}
(t_{Eon} = integrating time for E_{on})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	700	V
I_C (100%) =	40	A
t_{don} =	0,10	µs
t_{Eon} =	0,12	µs

Figure 3 Output inverter IGBT

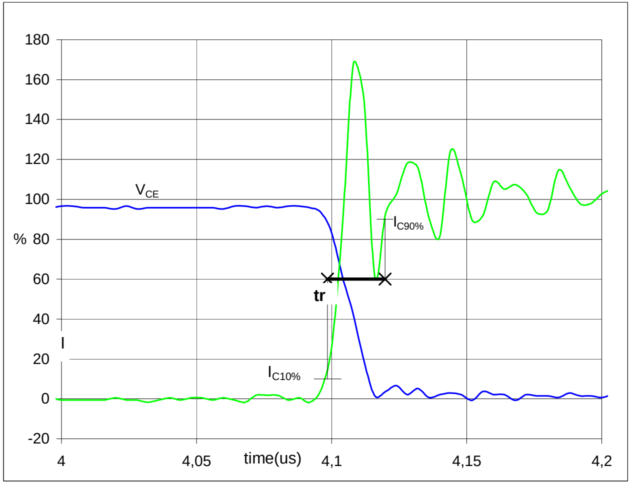
Turn-off Switching Waveforms & definition of t_f



V_C (100%) =	700	V
I_C (100%) =	40	A
t_f =	0,01	µs

Figure 4 Output inverter IGBT

Turn-on Switching Waveforms & definition of t_r

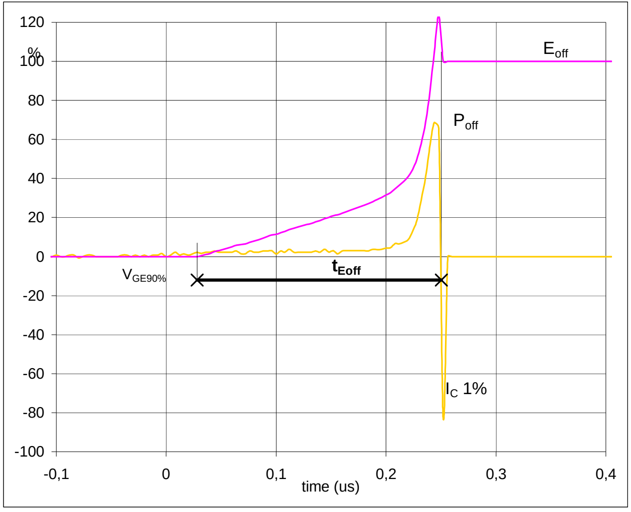


V_C (100%) =	700	V
I_C (100%) =	40	A
t_r =	0,01	µs

Switching Definitions BUCK MOSFET

Figure 5 Output inverter IGBT

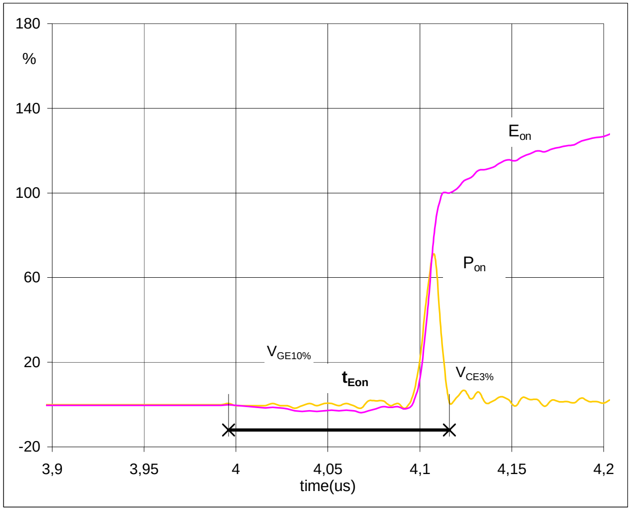
Turn-off Switching Waveforms & definition of t_{Eoff}



P_{off} (100%) = 28,08 kW
E_{off} (100%) = 0,23 mJ
t_{Eoff} = 0,22 μs

Figure 6 Output inverter IGBT

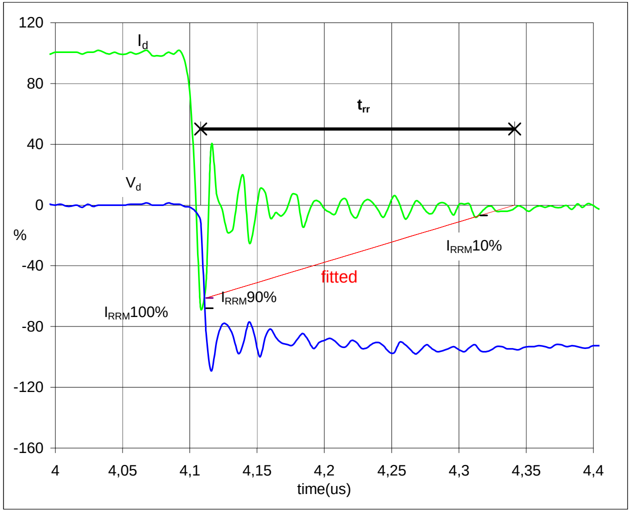
Turn-on Switching Waveforms & definition of t_{Eon}



P_{on} (100%) = 28,08 kW
E_{on} (100%) = 0,10 mJ
t_{Eon} = 0,12 μs

Figure 7 Output inverter IGBT

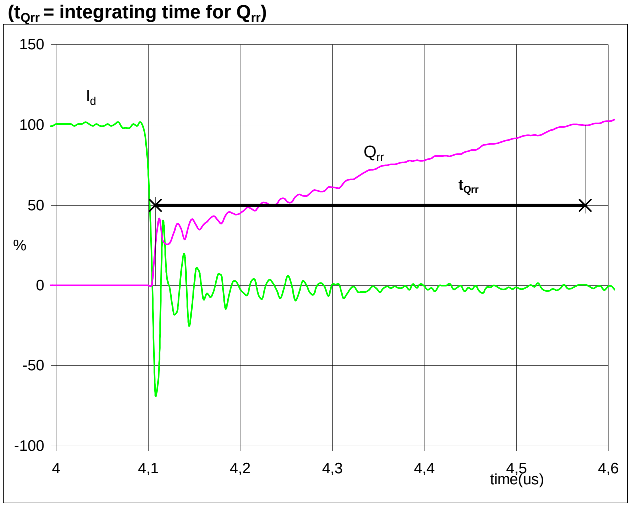
Turn-off Switching Waveforms & definition of t_{rr}



V_d (100%) = 700 V
I_d (100%) = 40 A
I_{RRM} (100%) = -34 A
t_{rr} = 0,01 μs

Figure 8 Output inverter FWD

Turn-on Switching Waveforms & definition of t_{Qrr}
(t_{Qrr} = integrating time for Q_{rr})

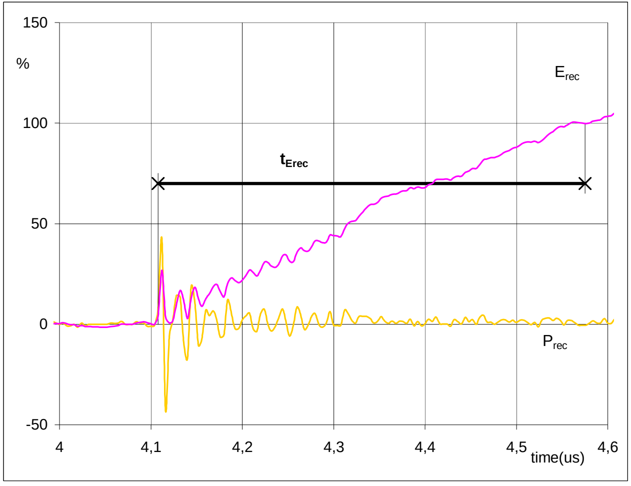


I_d (100%) = 40 A
Q_{rr} (100%) = 0,12 μC
t_{Qrr} = 0,47 μs

Switching Definitions BUCK MOSFET

Figure 9 Output inverter FWD

Turn-on Switching Waveforms & definition of t_{Erec}
(t_{Erec}= integrating time for E_{rec})

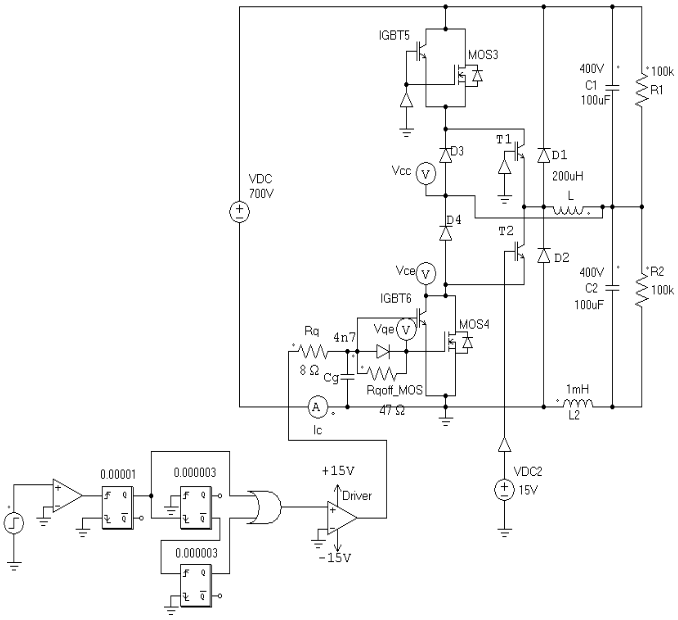


P_{rec} (100%) =	28,08	kW
E_{rec} (100%) =	0,01	mJ
t_{Erec} =	0,47	µs

Measurement circuits

Figure 11

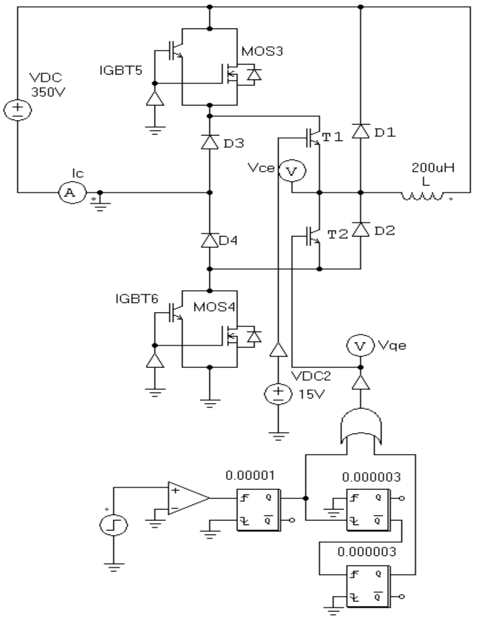
BUCK stage switching measurement circuit



Cg is included in the module

Figure 12

BOOST stage switching measurement circuit



Ordering Code and Marking - Outline - Pinout

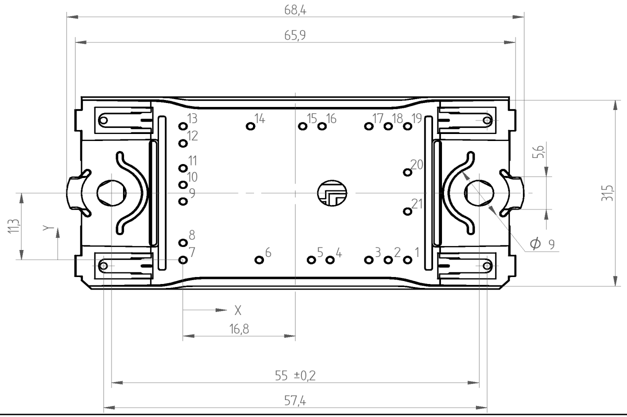
Ordering Code & Marking

Version	Ordering Code	in DataMatrix as	in packaging barcode as
without thermal paste 12mm housing	10-FZ06NPA070FP-P969F	P969F	P969F
without thermal paste 17mm housing	10-F006NPA070FP-P969F09	P969F09	P969F09
without thermal paste 12mm housing with pressfit	10-PZ06NPA070FP-P969FY	P969FY	P969FY
without thermal paste 17mm housing with pressfit	10-P006NPA070FP-P969F09Y	P969F09Y	P969F09Y

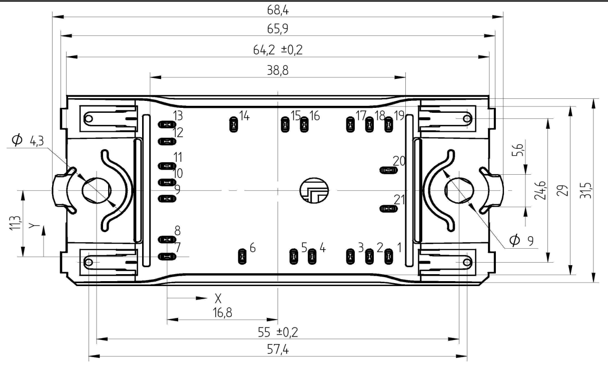
Outline

Pin table

Pin	X	Y
1	33,6	0
2	30,7	0
3	27,8	0
4	22	0
5	19,2	0
6	11,4	0
7	0	0
8	0	2,9
9	0	9,9
10	0	12,7
11	0	15,5
12	0	19,7
13	0	22,6
14	10,1	22,6
15	17,9	22,6
16	20,8	22,6
17	27,8	22,6
18	30,7	22,6
19	33,6	22,6
20	33,6	14,8
21	33,6	8,2

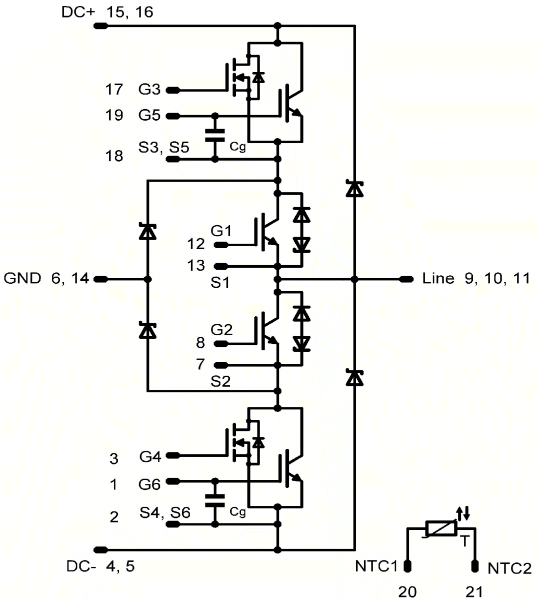


Solder pin



Pressfit

Pinout



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Datasheet Status	Product Status	Definition
Target	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice. The data contained is exclusively intended for technically trained staff.
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